

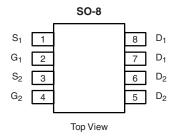
Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
30	0.036 at V _{GS} = 10 V	5.9			
30	0.053 at V _{GS} = 4.5 V	4.9			

FEATURES

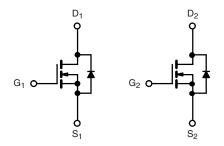
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4936ADY-T1-E3 (Lead (Pb)-free)

Si4936ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ °C, unles	ss otherwise r	noted		_
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		
Gate-Source Voltage		V _{GS}	± 20		V
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	5.9	4.4	
	T _A = 70 °C		4.7	3.6	
Pulsed Drain Current		I _{DM}	± 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9	
	T _A = 25 °C	P _D	2.0 1.1		W
Maximum Power Dissipation ^a	T _A = 70 °C] ' ['] D	1.3	0.7	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mariana Indiana Indian	t ≤ 10 s	R _{thJA}	50	62.5		
Maximum Junction-to-Ambient ^a	Steady State	' ¹thJA	90	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	32	40		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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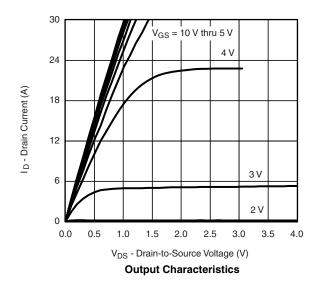
SPECIFICATIONS $T_J = 25$ °	C, unless o	therwise noted					
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μΑ	
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V, I _D = 5.9 A		0.032	0.036	0	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 4.9 \text{ A}$		0.042	0.053	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 5.9 A		15		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			13	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5.9 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_{gd}			2.0			
Turn-On Delay Time	t _{d(on)}			6	12		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		14	25		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		30	60	ns	
Fall Time	t _f			5	10		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dI/dt = 100 A/μs		30	60		

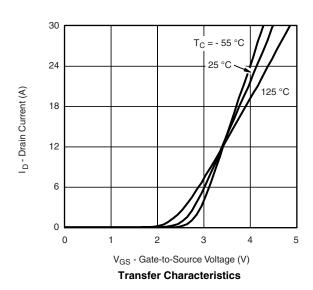
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

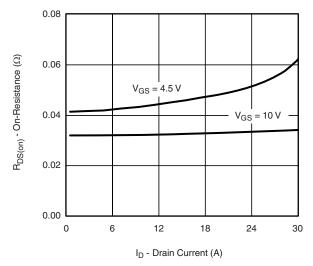
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



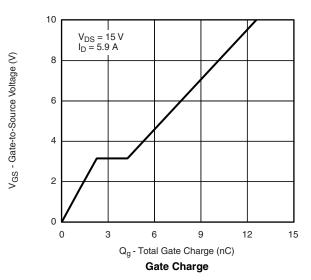


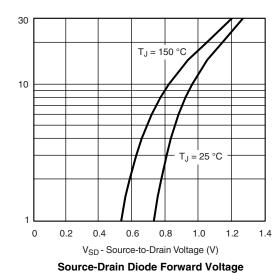


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



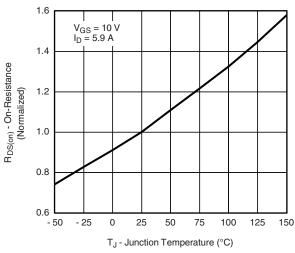
On-Resistance vs. Drain Current



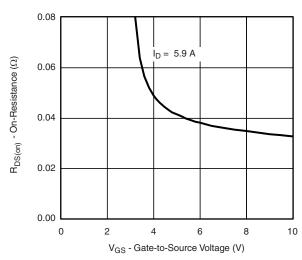


1000 800 C_{iss} 600 400 200 C_{rss} C_{oss} 200 0 6 12 18 24 30

 V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature



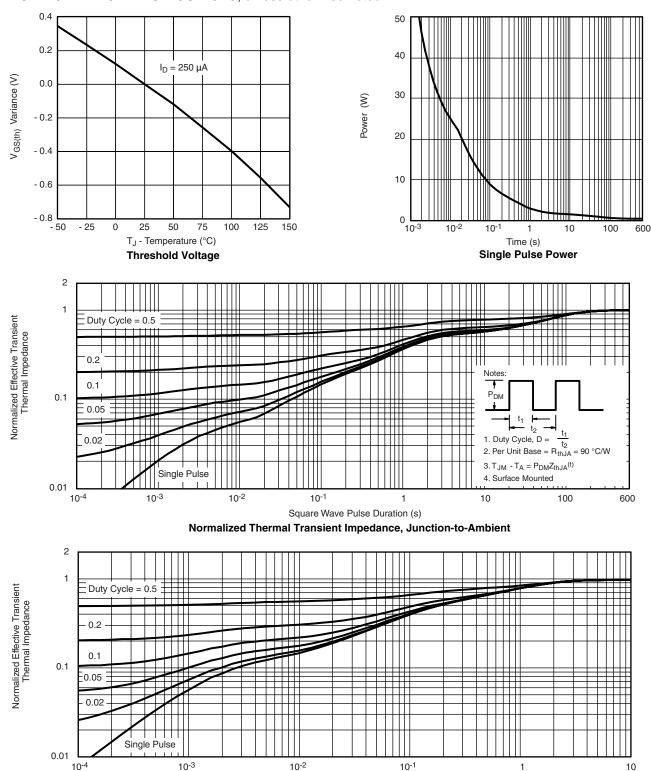
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

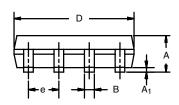
Normalized Thermal Transient Impedance, Junction-to-Foot

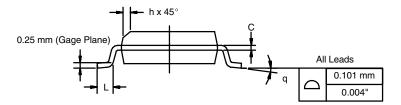
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







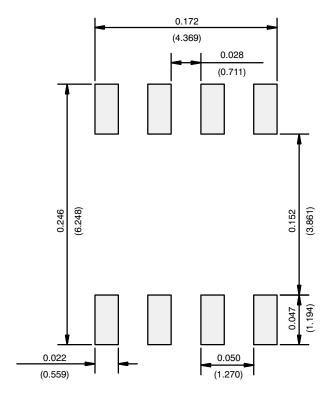
	MILLIM	IETERS	INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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